PCN Number: 202			202)240405000.2						P(CN ate:	April 08, 2024		
Title: Qualification of a new Di options for select device							evision	, Data sl	neet and	add	itional <i>A</i>	Assembly BOM		
Customer Change Ma					nag	ement	team	Dept:	Q	Quality Services				
Proposed 1 st Ship Octobe Date: 2024					er O	5,	Sample requests accepted until: May 08, 2024*			May 08, 2024*				
*Sar	mple	request	s rec	eive	d after l	Мау	08, 20	24 will r	not be sup	poi	ted.			
Cha	nge	Type:												
	Asse	embly Sit	te			\boxtimes	Design				Wafer Bump Material			
	Asse	embly Pr	oces	S		\boxtimes	Data Sheet				Wafe	Wafer Bump Process		
	Assembly Materials						Part r	umber (change		Wafe	Wafer Fab Site		
	Mechanical Specification						Test S	Test Site			Wafe	Wafer Fab Material		
	Packing/Shipping/Labeling						Test Process				Wafe	Wafer Fab Process		
							PCN	Detai	ls					

Description of Change:

Texas Instruments is pleased to announce the qualification of a new die revision, data sheet in addition to an Assembly BOM option for the devices listed below.

Construction differences are as follows:

	Current - TITL	Current - MLA	Proposed
Wire diam/type	0.96mil Au	0.96milAu	0.80mil Cu
	(Die to Die)	(Die to Die)	(Die to Die &
	1.0mil Cu	1.0mil Cu	Die to Lead)
	(Die to Lead)	(Die to Lead)	
Mold compound	4221499	4211880	4211880

This particular PCN is related to TI's transition of dual-channel isolated gate drivers in narrow body package (16D) to a newly-designed circuit and to TI's most efficient manufacturing processes and technology. The newly-designed circuit includes improvements to robustness in common automotive and industrial applications. Changes in the datasheet are summarized in the table below and the new datasheet is available at www.ti.com/product/UCC21222-Q1. TI additionally offers a transition guide to ensure complete understanding of system considerations which is available upon request in the SDP (supporting data package). The changes to the manufacturing processes and technology underscore our commitment to product longevity and supply continuity.

Qual details are provided in the Qual Data Section.

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below.



UCC21222-Q1

SLUSDA5B - FEBRUARY 2018 - REVISED APRIL 2024

С	hanges from Revision A (February 2024) to Revision B (April 2024)	Page
•	Updated section Features	1
•	Updated section Description	1
•	Updated DIS pin and DT pin descriptions in section Pin Configuration and Functions	3
•	Updated section 5.1 Absolute Maximum Ratings	4
•	Updated section 5.2 ESD Ratings (Automotive)	4
•	Updated section 5.3 Recommended Operating Conditions	
•	Updated section 5.4 Thermal Information	
•	Updated section 5.5 Power Ratings	5
•	Updated section 5.6 Insulation Specifications	6
•	Deleted Safety-Related Certification section	7
•	Updated section 5.7 Safety Limiting Values	7
•	Updated section 5.8 Electrical Characteristics	
•	Updated section 5.9 Switching Characteristics	
•	Changed section name from Thermal Derating Curves to Insulation Characteristics Curves	
•	Updated section Typical Characteristics	
•	Updated section Programmable Dead Time	16
•	Updated timings called out in section Power-Up UVLO Delay to OUTPUT	
•	Updated internal resistor structure in section Functional Block Diagram	
•	Updated section Input and Output Logic Table	
•	Updated section Input Stage to match new specifications	
•	Updated section Output Stage to address minimum pulse widths	
•	Updated ESD cell structure figure in section Diode Structure in the UCC21222-Q1	
•	Updated section Disable Pin verbiage	
•	Updated new deadtime equation in section Connecting a Programming Resistor between DT and GN Pins	D
•	Updated deadtime value due to change in deadtime equation in section Select Dead Time Resistor ar Capacitor	nd

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
UCC21222-Q1	SLUSDA5A	SLUSDA5B	http://www.ti.com/product/ UCC21222-Q1

Reason for Change:

Continuity of Supply

These changes are to transition TI's dual-channel isolated gate drivers in narrow body package (16D) to TI's most efficient manufacturing processes and technology, underscoring our commitment to product longevity and supply continuity. Additionally, the newlydesigned circuit includes improvements to robustness in common automotive and industrial applications, underscoring our commitment to continuous improvements in both product quality and end system robustness.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	No Change	No Change	No Change

Changes to product identification resulting from this PCN:

Die Rev:

Current New

Die Rev [2P]	Die Rev [2P]
В, С	A
Product Affected:	
UCC21222QDRQ1	

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 Rev. H and JEDEC Guidelines)
Approve Date 21-December-2023

Product Attributes

Attributes	Qual Device:	QBS Package Reference:	QBS Package Reference:	QBS Process Reference:	QBS Product Reference:
Attributes	UCC21330BQDRQ1	<u>IS06721BQDRQ1</u>	TLV9022QDRQ1	UCC23513QDWYQ1	UCC21551CQDWKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Interface	Signal Chain	Power Management	Power Management
Wafer Fab Supplier	RFAB, RFAB, RFAB	MH8, MH8	RFAB	RFAB, RFAB	RFAB, RFAB, RFAB
Assembly Site	MLA	MLA	MLA	TAI	MLA
Package Group	SOIC	SOIC	-	SOIC	SOIC
Package Designator	D	D	D	DWY	DWK
Pin Count	16	8	8	6	14

QBS: Qual By Similarity

Qual Device UCC21330BQDRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

			Dui	u Di	opiayca c	io. I talli	001 01	1013 / 10141	ournpic of	20 / 10tai	idiica	
Туре	#	Test Spec	Min	SSI	Test Name	Condition	Duration	Qual Device:	QBS Package Reference:	QBS Package Reference:	QBS Process Reference:	QBS Product Reference:
7,00			Qty	Lot	Test Hand	Condition		UCC21330BQDRQ1	IS06721BQDRQ1	TLV9022QDRQ1	UCC23513QDWYQ1	UCC21551CQDWKRQ1
Test Group	A - Acc	elerated Enviror	nment S	tress Te	sts			36.				
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C		23	No Fails	No Fails	1-	-
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C		No Fails	-	-	12	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours		3/231/0	3/231/0	-	
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-	-	
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	2	2	3/231/0	12	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	3/231/0	-	-

HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-	-	-
Test Group	B - Acce	lerated Lifetim	e Simula	tion Test	ts			20.	20			
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	-	-	3/231/0	1/77/0
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	•	-	-	3/2400/0	-
Test Group	C - Pack	age Assembly	Integrity	Tests					40	150		00
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/228/0	3/90/0	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/228/0	3/90/0	-	-
SD	C3	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0	3/30/0	3/30/0	-	-
Test Group	D - Die F	abrication Relia	ability Te	sts								
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
вті	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verificatio	n iests									
Test Group ESD	E - Elect	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
		AEC Q100-		3	ESD HBM ESD CDM	-		1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E2	AEC Q100- 002 AEC Q100-	1			- Per AEC Q100-004	Volts 500					

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7 eV: 150 C/1 k Hours, and 170 C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

		Data Disp	лауси	as. 1	Number of lots / 1	otal sample size /	i Otal Tall	icu
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>ISO6763QDWRQ1</u>
Test Gr	oup A - A	Accelerated Environment Str	ess Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-
HAST	A2.1.4		3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	•
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
тс	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0
тс	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0
тс	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0

HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0			
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL,	Post stress cross section	Completed	-			
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0			
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0			
Test Group B - Accelerated Lifetime Simulation Tests											
Test Gr	oup C - F	Package Assembly Integrity	Tests								
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0			
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0			
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-			
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-			
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-			
Test Gr	oup D - [Die Fabrication Reliability Tes	its								
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements			
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements			
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements			
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements			
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements			
Test Gr	oup E - E	Electrical Verification Tests									

QBS: Qual By Similarity

Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

ZVEI ID reference: SEM-PA-11, SEM-PA-08, SEM-DE-02, SEM-DE-03, SEM-DS-01

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

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